JIEJIE MICROELECTRONICS CO., LTD.

TYN50H-1200SJ 50A SCR

Rev.A.2.1

ESCRIPTION:

With high ability to withstand the shock loading of large current, TYN50H-1200SJ SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is -0.002eY(2.7(IO)-1.2(vel(l)6(i)14(t)7(e)1O)-1o-3(a)-3(a)10(nc)de)9(o)d10(hi-8(er

Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W

Peak pulse voltage
(T_j=25 ; non-repetitive,off-state;FIG.7)

VW WWW W

FIG.1: Maximum power dissipation versus RMS on-state current

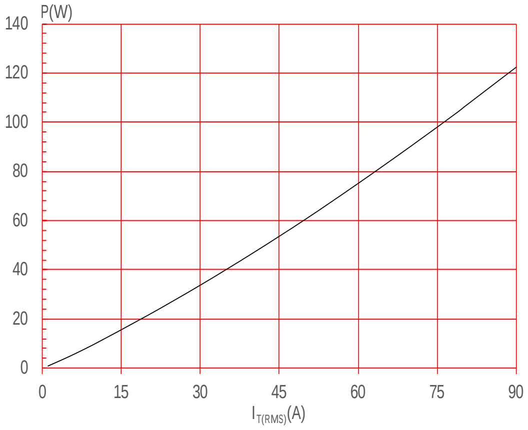
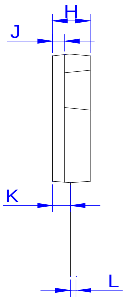


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50		16.10	0.610		0.634
B1	3.10		3.50	0.122		0.138
C						
D	2.90		3.30	0.114		0.130
E	1.90		2.30	0.075		0.091
F	1.00		1.40	0.039		0.055
G						
H	4.80		5.20	0.189		0.205
J						
K						
L						

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